

Notebook

Table of Contents

POWER MANAGEMENT, Charger Power.....	3
POWER MANAGEMENT, CPU Power.....	6
POWER MANAGEMENT, Other Device Power.....	9
POWER MANAGEMENT, System-,DDR-,Chipset-,VGA-Power.....	10
SYSTEM HARDWARE, IrDA Transceiver.....	14
SYSTEM HARDWARE, Load Switch.....	15
SYSTEM HARDWARE, Opto Sensor.....	16
SYSTEM HARDWARE, Protection.....	17

Notebook

VISHAY components used for Notebook functions include:

- Power MOSFETS
 - Controller ICs
 - LDOs
 - IrDA and IR Receiver Modules
 - Load and Signal Switches
 - Switching Diodes and Rectifiers
 - Transient/Overvoltage Protection Devices
 - ESD Protection Devices
 - Capacitors
 - Resistors
 - NTC and PTC Thermistors
 - Inductors/EMI Filters
 - Secondary Protection Fuses
-

Application Overview

Notebook computer design is separated into two segments: Power and Hardware. The Power Segment involves hardware device power sources. For power sources, using a switching mode is an excellent way to improve converter efficiency. High current is its key feature. Power sources that use this technology include CPUs, DDR systems, chipsets, chargers, and VGA power sources. Low-dropout linear power is another solution for converter efficiency. Its main benefits are lower prices and simple circuitry. The Hardware Segment can be regarded as a non-power segment. Types of hardware include SD cards, USB ports, fingerprint recognition systems, remote controls, audio controls, touchscreens and touchpads, ambient light sensors, S-video ports, and wireless transmission systems such as IrDA® and Bluetooth®. Some of these need similar functions such as ESD protection, current limiting, and load switching. Different solutions based on different specifications are suggested.

Notebook : POWER MANAGEMENT, Charger Power

Adaptor / Battery Switch

Product Name	Status	Description	Features	Package	Q-Level
Si4413ADY	NEW	P-Channel 30-V (D-S) MOSFET VDS = -30V; VGS = ± 20V	Low rDS(on) ID=15A; rDS(on)=0.0075Ω Qgd= 61nC; VGStH= -1 V;	SMD SO-8	
Si4425BDY		P-Channel 30-V (D-S) MOSFET VDS = -30V; VGS = ± 20V	VGS = ± 20V ID=-11.4A; rDS(on)=0.012Ω Qgd= 64nC; VGStH= -1 V;	SMD SO-8	
Si4431BDY		P-Channel 30-V (D-S) MOSFET VDS = -30V; VGS = ± 20V	VGS = ± 20V ID=-7.5A; rDS(on)=0.030Ω Qgd= 13nC; VGStH= -1 V;	SMD SO-8	
Si4435BDY		P-Channel 30-V (D-S) MOSFET VDS = -30V; VGS = ± 20V	VGS = ± 20V ID=-9.1A; rDS(on)=0.020Ω Qgd= 33nC; VGStH= -1 V;	SMD SO-8	
Si4483EDY		P-Channel 30-V (D-S) MOSFET With 3-kV ESD Protection VDS = -30V; VGS = ± 25V	High VGS = ± 25V ID=-14A; rDS(on)=0.0085Ω VGStH = -1.0 V;	SMD SO-8	
Si4825DY		P-Channel 30-V (D-S) MOSFET VDS = -30V; VGS = ± 25V	High VGS = ± 25V ID=-11.5A; rDS(on)=0.014Ω Qg=15nC; VGStH= -1 V;	SMD SO-8	
Si4835BDY		P-Channel 30-V (D-S) MOSFET VDS = -30V; VGS = ± 25V	High VGS = ± 25V ID=-9.6A; rDS(on)=0.018Ω Qg=25nC; VGStH= -1 V;	SMD SO-8	
Si4890DY		N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 20V	High VGS = ± 25V ID=-11A; rDS(on)=0.012Ω Qg=14.2nC; VGStH=0.8 V;	SMD SO-8	
Si7459DP		P-Channel 30-V (D-S) MOSFET VDS = -30V; VGS = ± 25V Low Thermal Resistance PowerPAK®	Low rDS(on), high VGS ID=-22A; rDS(on)=0.0068Ω Qg= 113nC; VGStH= -1V	SMD PowerPAK SO-8	
Si7945DP		Dual P-Channel 30-V (D-S) MOSFET VGS = ± 20V; TrenchFET® Power MOSFET	Low rDS(on); ID=-10.9A; rDS(on)=0.020Ω Qg= 49 nC; VGStH= -1 V	SMD PowerPAK SO-8	

Dual Mofets

Product Name	Status	Description	Features	Package	Q-Level
Si4830 ADY		Dual N-Ch. 30-V (D-S) MOSFET w. SCHOTTKY DUAL; With 2 A SCHOTTKY; VDS = 30V; VGS = ± 20V	VGS = ± 20V ID=7.5A; rDS(on)=0.030Ω Qgd= 2.5nC; VGStH= 1.4 V;	SMD SO-8	
Si4834BDY		Dual N-Ch. 30-V (D-S) MOSFET w. SCHOTTKY DUAL; With 2 A SCHOTTKY; VDS = 30V; VGS = ± 20V	VGS = ± 20V ID=7.5A; rDS(on)=0.030Ω Qgd= 2.5nC; VGStH= 0.8 V;	SMD SO-8	
Si4914DY		Dual N-Ch 30-V (D-S) MOSFET w. SCHOTTKY DUAL; With 2 A SCHOTTKY; VDS = 30V; VGS = ± 20V	ID = 7 A / 7.4 A rDS(on)=0.032Ω / 0.027Ω Qgd=1.7 / 2.2nC; VGStH=1V	SMD SO-8	
Si4952DY		Dual N-Channel 25-V (D-S) MOSFET DUAL VDS = 25V; VGS = ± 16V	VGS = ± 20V ID=7.5A; rDS(on)=0.030Ω Qgd= 2.5nC; VGStH= 0.8 V;	SMD SO-8	

High-Side MOSFETs

Product Name	Status	Description	Features	Package	Q-Level
Si4800BDY		N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 25V High-Efficient PWM Optimized	High VGS = ± 25V ID=9A; rDS(on)=0.030Ω Qgd= 3.5nC; VGStH= 0.8 V;	SMD SO-8	
Si4812BDY		N-Ch. 30-V (D-S) MOSFET w. SCHOTTKY With 1.4 A SCHOTTKY;	VGS = ± 20V ID=9.5A; rDS(on)=0.021Ω	SMD SO-8	

Product Name	Status	Description	Features	Package	Q-Level
		VDS = 30V; VGS = ± 20V	Qgd= 2.6nC; VGSth= 1 V;		
Si4835BDY		P-Channel 30-V (D-S) MOSFET VDS = -30V; VGS = ± 25V	High VGS = ± 25V ID=-9.6A; rDS(on)=0.018Ω Qg=25nC; VGSth= -1 V;	SMD SO-8	
Si7230DN	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V PWM Optimized	High power dissipation ID=14A; rDS(on)=0.016Ω Qgd= 4.3nC; VGSth= 1 V;	SMD PowerPAK 1212	
Si7326DN	NEW	N-Ch. 30-V (D-S) Fast Switching MOSFET VDS = 30V; VGS = ± 20V	High power dissipation ID=10A; rDS(on)=0.030Ω Qgd= 3.5nC; VGSth= 0.8 V;	SMD PowerPAK 1212	

Inductors

Product Name	Status	Description	Features	Package	Q-Level
IHLP2525CZ-01		Inductor; High Current; Low Profile; Small Outline Package; Fully Shielded; Miniature Power	Profile height ≤ 3 mm 0.1 μH to 10 μH IDC up to 60 A	SMD 2525 7.3x7.3x3.0mm	
IHLP4040DZ-01		Inductor; High Current; Low Profile; Small Outline Package; Fully Shielded;	Profile height ≤ 4mm 0.19 μH to 10 μH IDC up to 90 A	SMD 4040 11.5x11.5x4.0mm	
IHLP4040DZ-11		Inductor; High Current; Low Profile; Small Outline Package; Fully Shielded;	Profile height ≤ 4mm 0.19 μH to 100 μH IDC up to 46 A	SMD 4040 11.5x11.5x4.0mm	
IHLP5050CE-01		Inductor; High Current; Low Profile; Small Outline Package; Fully Shielded;	Profile height ≤ 3.5mm 0.1 μH to 10 μH IDC up to 84 A	SMD 5050 13.5x13.5x3.5mm	

Low Side MOSFETs

Product Name	Status	Description	Features	Package	Q-Level
Si4800BDY		N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 25V High-Efficient PWM Optimized	High VGS = ± 25V ID=9A; rDS(on)=0.030Ω Qgd= 3.5nC; VGSth= 0.8 V;	SMD SO-8	
Si4812BDY		N-Ch. 30-V (D-S) MOSFET w. SCHOTTKY With 1.4 A SCHOTTKY; VDS = 30V; VGS = ± 20V	VGS = ± 20V ID=9.5A; rDS(on)=0.021Ω Qgd= 2.6nC; VGSth= 1 V;	SMD SO-8	
Si7230DN	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V PWM Optimized	High power dissipation ID=14A; rDS(on)=0.016Ω Qgd= 4.3nC; VGSth= 1 V;	SMD PowerPAK 1212	
Si7326DN	NEW	N-Ch. 30-V (D-S) Fast Switching MOSFET VDS = 30V; VGS = ± 20V	High power dissipation ID=10A; rDS(on)=0.030Ω Qgd= 3.5nC; VGSth= 0.8 V;	SMD PowerPAK 1212	

Resistors

Product Name	Status	Description	Features	Package	Q-Level
WSL2010-18		1 Watt Current sensing Resistor Power Metal Strip® Resistors; Low Resistance Value;	High power & reliability R=0.001Ω to 0.2Ω TCR ≤ 20ppm	SMD 2010 5.08x2.54x0.635	
WSL2512-18		2 Watt Current sensing Resistor Power Metal Strip® Resistors; Low Resistance Value;	High power & reliability R=0.001Ω to 0.2Ω TCR ≤ 20ppm	SMD 2512 6.36x3.18x0.635	
WSP1206	NEW	1 Watt Power Metal Strip® Resistors; Very High Power- Small Size; Current Sensing;	High power & reliability R=0.001Ω to 0.2Ω	SMD 1206 3.2x1.6x0.635mm	

Schottky Diodes

Product Name	Status	Description	Features	Package	Q-Level
B140		Schottky Barrier Rectifier; Low Profile; Guardring for overload protection; High Surge Capabilities;	VRRM = 40 V; IF = 1 A, VF = 0.52 V,	SMD DO-214AC (SMA) 5.28x2.8x2.3mm	

Product Name	Status	Description	Features	Package	Q-Level
B240 A		High-Current Density Schottky Rectifier High Efficiency; Low Power Loss; Low Profile	VRRM = 40 V; IF = 2 A, VF = 0.5 V,	SMD DO-214AC (SMA) 5.28x2.8x2.3mm	
B340 A		High-Current Density Schottky Rectifier High Efficiency; Low Power Loss; RoHS-Compliant	VRRM = 40 V; IF = 3A, VF = 0.5 V,	SMD DO-214AC (SMA) 5.28x2.8x2.3mm	
MSS1P4		Schottky Barrier Rectifiers SMD; #SMP# Series;	VRRM = 40 V; IF = 1 A; VF = 0.41 V;	SMD MicroSMP 2.7x1.4x0.75mm	
SS10P4	NEW	Schottky Barrier Rectifiers; SMD; High Current Density; #SMP# Series;	High power /small package VRRM = 40 V; IF = 10 A;VF = 0.384 V	SMD TO-277A (SMPC) 6.65x4.75x1.2mm	
SS1P4	NEW	Schottky Barrier Rectifiers; SMD; High Current Density; #SMP# Series;	Small package VRRM = 40 V; IF = 2 A, VF = 0.4 V,	SMD DO-220AA (SMP) 4x2.18x1.15mm	
SS2P4	NEW	Schottky Barrier Rectifiers; SMD; High Current Density; #SMP# Series;	Small package VRRM = 40 V; IF = 2 A, VF = 0.43 V,	SMD DO-220AA (SMP) 4x2.18x1.15mm	
SS3P4	NEW	Schottky Barrier Rectifiers; SMD; High Current Density;#SMP# Series;	Small package VRRM = 40 V; IF = 3A, VF = 0.5 V,	SMD DO-220AA (SMP) 4x2.18x1.15mm	
SS5P4	NEW	Schottky Barrier Rectifiers; SMD; High Current Density;#SMP# Series;	High power /small package VRRM = 40 V; IF = 5 A, VF = 0.403 V,	SMD TO-277A (SMPC) 6.65x4.75x1.2mm	
SS8P4C	NEW	Schottky Barrier Rectifiers; SMD; High Current Density;#SMP# Series; Dual Common-Cathode;	High power /small package VRRM = 40 V; IF = 8 A, VF = 0.42 V,	SMD TO-277A (SMPC) 6.65x4.75x1.2mm	
SSC54	NEW	Schottky Barrier Rectifiers; SMD; High Current Density;	Small Outline VRRM = 40 V; IF = 5 A, VF = 0.36V,	SMD DO-220AA (SMC) 8.13x6.22x2.62mm	

Signal Mosfet

Product Name	Status	Description	Features	Package	Q-Level
2N7002K		N-Ch 60-V (D-S)MOSFET; 2KV ESD protected Low On-Resistance; Low Threshold; Low Input Capacitance; Fast Switch	VDS = 60 V; VGS = 20 V; rDS(on) = 4 Ohms, ID = 0.3A, VGSth = 1 V	SMD TO-236 (SOT-23)	

Switch Diodes

Product Name	Status	Description	Features	Package	Q-Level
1N4148WS-V		Small Signal Fast Switching Diode; Silicon epitaxial planar diode; RoHS-Compliant;	VRRM = 75 V; IF = 0.15A; VF = 1.2 V;	SMD SOD323 2.85x1.5x1.15mm	
BAT54 A		Schottky Barrier Diode; DUAL; Miniature; for high speed switching; clamping; and circuit protection.	Dual, VRRM = 30 V; IF = 0.2 A, VF = 0.5 V,	SMD TO-236 (SOT-23) 3.1x2.6x1.15mm	Std.
BAT54 A-V		Small Signal Schottky Diodes; Single & Dual Schematics; Very Low Turn-On and Fast Switching	Dual, VRRM = 30 V; IF = 0.2 A, VF = 0.8 V,	SMD TO-236 (SOT-23) 3.0x2.5x1.1mm	Thin Pack
BAT54 AW		Schottky Barrier Diode; DUAL; Miniature;	DUAL;VRRM = 30 V, IF = 0.2 A, VF = 0.5 V,	SMD SOT-323 2.2x2.2x1.0mm	
MBR0530		Schottky Diodes; Fast Switching; Ultra Low Forward Voltage drop;	VRRM = 30 V; IF = 0.5 A, VF = 0.35 V;	SMD SOD123 3.85x1.7x1.35mm	

Notebook : POWER MANAGEMENT, CPU Power

High-Side MOSFETs

Product Name	Status	Description	Features	Package	Q-Level
Si4386DY		N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 20V	Low Qgd; low rDS(on) ID=16A; rDS(on)=0.0095Ω Qgd = 3.0 nC;	SMD SO-8	
Si4392DY		N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 20V	Low Qgd ID=12.5A; rDS(on)=0.01375Ω Qgd = 2.6 nC;	SMD SO-8	
Si4682DY	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V	Low Qgd ID=12A; rDS(on)=0.0135Ω Qgd = 3.1 nC;	SMD SO-8	
Si4684DY	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 12V	Low Qgd ID=12A; rDS(on)=0.0135Ω Qgd = 2.8 nC;	SMD SO-8	
Si4686DY	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V Extremely Low Qgd WFET® Technology	Low Qgd ID=13.8A; rDS(on)=0.014Ω Qgd = 2.8 nC;	SMD SO-8	
Si7386DP		N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 20V	Low Qgd, low rDS(on) ID=19A; rDS(on)=0.0095Ω Qgd = 3.0 nC	SMD PowerPAK SO-8	
Si7392DP		N-Ch. Reduced Qg, Fast Switching WFET® VDS = 30V; VGS = ± 20V	Low Qgd ID=15A; rDS(on)=0.01375Ω Qgd = 2.6 nC	SMD PowerPAK SO-8	
Si7682DP	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V 100% Rg Tested	Low Qgd ID=17.5A; rDS(on)=0.013Ω Qgd = 3.1 nC;	SMD PowerPAK SO-8	
Si7686DP	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V Low Thermal Resistance PowerPAK®	Low Qgd ID=17.9A; rDS(on)= 0.014Ω Qgd = 2.8 nC;	SMD PowerPAK SO-8	
SUD50N03-10P		N-Ch 30-V (D-S), 175°C, MOSFET; PWM Optimized; VDS = 30 V, VGS = ±20 V	ID=63A; rDS(on)=0.013Ω Qgd = 5 nC	SMD TO-252 DPAK	

Inductors

Product Name	Status	Description	Features	Package	Q-Level
IHLP4040DZ-01		Inductor; High Current; Low Profile; Small Outline Package; Fully Shielded;	Profile height ≤ 4mm 0.19 μH to 10 μH IDC up to 90 A	SMD 4040 11.5x11.5x4.0mm	
IHLP4040DZ-11		Inductor; High Current; Low Profile; Small Outline Package; Fully Shielded;	Profile height ≤ 4mm 0.19 μH to 100 μH IDC up to 46 A	SMD 4040 11.5x11.5x4.0mm	
IHLP5050CE-01		Inductor; High Current; Low Profile; Small Outline Package; Fully Shielded;	Profile height ≤ 3.5mm 0.1 μH to 10 μH IDC up to 84 A	SMD 5050 13.5x13.5x3.5mm	

Low-Side MOSFETs

Product Name	Status	Description	Features	Package	Q-Level
Si4336DY		N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V	Low rDS(on) ID=16.3A; rDS(on)=0.0067Ω VGSth = 1.0 V;	SMD SO-8	
Si4430BDY		N-Channel 30-V MOSFET VDS = 30V; VGS = ± 20V	Low rDS(on) ID=20A; rDS(on)=0.006Ω VGSth = 1.0 V;	SMD SO-8	
Si4634DY	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V	low rDS(on), high Vast ID=16.3A; rDS(on)=0.0067Ω VGSth = 1.4 V;	SMD SO-8	
Si4874BDY	NEW	N-Channel 30-V MOSFET VDS = 30V; VGS = ± 20V	Low rDS(on) ID=16A; rDS(on)=0.0085Ω VGSth = 1 V	SMD SO-8	

Product Name	Status	Description	Features	Package	Q-Level
Si7336 ADP	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V Ultra Low (ON) Resistance;	Low rDS(on) ID=30A; rDS(on)=0.0040Ω VGSth = 1 V	SMD PowerPAK SO-8	
Si7634BDP	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V	Low rDS(on), high Vast ID=23A; rDS(on)=0.0076Ω VGSth = 1.5 V	SMD PowerPAK SO-8	
Si7636DP		N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V Ultra Low (ON) Resistance	Low rDS(on) ID=28A; rDS(on)=0.0048Ω VGSth = 1 V	SMD PowerPAK SO-8	
SUD50N03-06 AP		N-Channel 30-V (D-S) MOSFET Optimized for Low#Side Synch. Rectif. VDS = 30 V, VGS = ±20 V	Low rDS(on) ID=30A; rDS(on)=0.0078Ω VGSth = 1.2 V	SMD TO-252 DPAK	

Resistors

Product Name	Status	Description	Features	Package	Q-Level
WSL2010-18		1 Watt Current sensing Resistor Power Metal Strip® Resistors; Low Resistance Value;	High power & reliability R=0.001Ω to 0.2Ω TCR ≤ 20ppm	SMD 2010 5.08x2.54x0.635	
WSL2512-18		2 Watt Current sensing Resistor Power Metal Strip® Resistors; Low Resistance Value;	High power & reliability R=0.001Ω to 0.2Ω TCR ≤ 20ppm	SMD 2512 6.36x3.18x0.635	
WSLP1206	NEW	1 Watt Power Metal Strip® Resistors; Very High Power- Small Size; Current Sensing;	High power & reliability R=0.001Ω to 0.2Ω	SMD 1206 3.2x1.6x0.635mm	

Schottky Diodes

Product Name	Status	Description	Features	Package	Q-Level
B140		Schottky Barrier Rectifier; Low Profile; Guardring for overload protection; High Surge Capabilities;	VRRM = 40 V; IF = 1 A, VF = 0.52 V,	SMD DO-214AC (SMA) 5.28x2.8x2.3mm	
B240 A		High-Current Density Schottky Rectifier High Efficiency; Low Power Loss; Low Profile	VRRM = 40 V; IF = 2 A, VF = 0.5 V,	SMD DO-214AC (SMA) 5.28x2.8x2.3mm	
B340 A		High-Current Density Schottky Rectifier High Efficiency; Low Power Loss; RoHS-Compliant	VRRM = 40 V; IF = 3A, VF = 0.5 V,	SMD DO-214AC (SMA) 5.28x2.8x2.3mm	
MSS1P4		Schottky Barrier Rectifiers SMD; #SMP# Series;	VRRM = 40 V; IF = 1 A; VF = 0.41 V;	SMD MicroSMP 2.7x1.4x0.75mm	
SS1P4	NEW	Schottky Barrier Rectifiers; SMD; High Current Density; #SMP# Series;	Small package VRRM = 40 V; IF = 2 A, VF = 0.4 V,	SMD DO-220AA (SMP) 4x2.18x1.15mm	
SS2P4	NEW	Schottky Barrier Rectifiers; SMD; High Current Density; #SMP# Series;	Small package VRRM = 40 V; IF = 2 A, VF = 0.43 V,	SMD DO-220AA (SMP) 4x2.18x1.15mm	
SS3P4	NEW	Schottky Barrier Rectifiers; SMD; High Current Density;#SMP# Series;	Small package VRRM = 40 V; IF = 3A, VF = 0.5 V,	SMD DO-220AA (SMP) 4x2.18x1.15mm	

Signal Switch

Product Name	Status	Description	Features	Package	Q-Level
2N7002K		N-Ch 60-V (D-S)MOSFET; 2KV ESD protected Low On-Resistance; Low Threshold; Low Input Capacitance; Fast Switch	VDS = 60 V; VGS = 20 V; rDS(on) = 4 Ohms, ID = 0.3A, VGSth = 1 V	SMD TO-236 (SOT-23)	

Switch Diodes

Product Name	Status	Description	Features	Package	Q-Level
1N4148WS-V		Small Signal Fast Switching Diode; Silicon epitaxial planar diode;	VRRM = 75 V; IF = 0.15A; VF = 1.2 V;	SMD SOD323	

Product Name	Status	Description	Features	Package	Q-Level
		RoHS-Compliant;		2.85x1.5x1.15mm	
BAT54 A		Schottky Barrier Diode; DUAL; Miniature; for high speed switching; clamping; and circuit protection.	Dual, VRRM = 30 V; IF = 0.2 A, VF = 0.5 V,	SMD TO-236 (SOT-23) 3.1x2.6x1.15mm	Std.
BAT54 A-V		Small Signal Schottky Diodes; Single & Dual Schematics; Very Low Turn-On and Fast Switching	Dual, VRRM = 30 V; IF = 0.2 A, VF = 0.8 V,	SMD TO-236 (SOT-23) 3.0x2.5x1.1mm	Thin Pack
BAT54 AW		SOT323:	DUAL;VRRM = 30 V, IF = 0.2 A, VF = 0.5 V,	SMD SOT-323 2.2x2.2x1.0mm	
MBR0530		Schottky Diodes; Fast Switching; Ultra Low Forward Voltage drop;	VRRM = 30 V; IF = 0.5 A, VF = 0.35 V;	SMD SOD123 3.85x1.7x1.35mm	

Thermistor NTC

Product Name	Status	Description	Features	Package	Q-Level
2381 615 1xxx		NTC Thermistors; Surface Mount; TCR from 6 to 2% even at higher temp. RoHS-Compliant;	2 k Ω -470 k Ω ;B25/85Tol.=1% RTol.@25°C <= 5 %; Ptot = 0.21 W	SMD 0805 EIA-Sizes	
2381 615 2xxx		NTC Thermistors; Surface Mount; Temperature Compensation	4.7 k Ω -100 k Ω ; RTol.@25°C <= 5 %; P=0.125 W; B25/85Tol.=1%	SMD 0603 EIA-Sizes	
2381 615 3xxx		NTC Thermistors; Surface Mount; Tolerance on B25/85 down to 1 %	2.2 k Ω to 100 k Ω ; 0.125 W RTol.@25°C = 5% to 1 %;	SMD 0603 EIA-Sizes	
2381 615 4xxx		NTC Thermistors; Surface Mount; Tolerance on B25/85 down to 1 %	4.7 k Ω to 100 k Ω ; 0.125 W RTol.@25°C = 5% to 1 %;	SMD 0402 EIA-Sizes	
2381 615 5xxx		NTC Thermistors; Surface Mount; Tolerance on B25/85 down to 1 %	2.2 k Ω to 680 k Ω , 0.21 W RTol.@25°C = 10% to 2 %;	SMD 0805 EIA-Sizes	
NTHS		NTC Thermistors; Monolithic Construction	R25 = 1 k Ω to 330 k Ω Tol.@25°C = 10 % to 1% B(25/75) = 3181 to 4247	SMD 0402 to 1206 EIA-Sizes	

Notebook : POWER MANAGEMENT, Other Device Power

LDOs

Product Name	Status	Description	Features	Package	Q-Level
Si9183		LDO Regulator; 150-mA CMOS; High Performance; Low Dropout;	Peak Output=300mA Dropout 0.135mV@150mA;	SMD Thin SOT-23	
SiP21103		LDO Regulator; 250-mA Ultra Low-Noise; With Discharge Option	Ultra Low Noise 30 μ V;	SMD MLP22	
SiP21104		LDO Regulator; 250-mA Ultra Low-Noise; With Error Flag and Discharge Option	Ultra Low Noise 75 μ V;	SMD MLP22	
SiP21106	NEW	LDO Regulator; 150-mA Low Noise Lower Noise output 60 μ V;	Low Noise 60 μ V;	SMD TSOT-23/TSC-75	
SiP21107		LDO Regulator; 150-mA Low Noise with flag for POK/ ERROR; function same as SiP21106	160°C Thermal Protection	SMD TSOT-23/TSC-75	
SiP21108		LDO Regulator; 150-mA Low Noise Output Adjust; function same as SiP21106,	330mA Short-Circuit Prot.	SMD TSOT-23/TSC-75	

Dual MOSFETs

Product Name	Status	Description	Features	Package	Q-Level
Si4830 ADY		Dual N-Ch. 30-V (D-S) MOSFET w. SCHOTTKY DUAL; With 2 A SCHOTTKY; VDS = 30V; VGS = ± 20V	VGS = ± 20V ID=7.5A; rDS(on)=0.030Ω Qgd= 2.5nC; VGSth= 1.4 V;	SMD SO-8	
Si4834BDY		Dual N-Ch. 30-V (D-S) MOSFET w. SCHOTTKY DUAL; With 2 A SCHOTTKY; VDS = 30V; VGS = ± 20V	VGS = ± 20V ID=7.5A; rDS(on)=0.030Ω Qgd= 2.5nC; VGSth= 0.8 V;	SMD SO-8	
Si4914DY		Dual N-Ch 30-V (D-S) MOSFET w. SCHOTTKY DUAL; With 2 A SCHOTTKY;	ID = 7 A / 7.4 A rDS(on)=0.032Ω / 0.027Ω Qgd=1.7 / 2.2nC; VGSth=1V	SMD SO-8	
Si4952DY		Dual N-Channel 25-V (D-S) MOSFET DUAL VDS = 25V; VGS = ± 16V	VGS = ± 20V ID=7.5A; rDS(on)=0.030Ω Qgd= 2.5nC; VGSth= 0.8 V;	SMD SO-8	
Si7844DP		Dual N-Channel 30-V (D-S) MOSFET; VGS= ± 20V; TrenchFET® Power MOSFET	High power dissipation; ID=10 A; rDS(on)= 0.030 Ω Qgd= 2.7nC; VGSth= 0.8 V;	SMD PowerPAK SO-8	

High-Side MOSFETs

Product Name	Status	Description	Features	Package	Q-Level
Si4386DY		N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 20V	Low Qgd, low rDS(on) ID=16A; rDS(on)=0.0095Ω Qgd = 3.0 nC;	SMD SO-8	
Si4392DY		N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 20V	Low Qgd ID=12.5A; rDS(on)=0.01375Ω Qgd = 2.6 nC;	SMD SO-8	
Si4682DY	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V	Low Qgd ID=12A; rDS(on)=0.0135Ω Qgd = 3.1 nC;	SMD SO-8	
Si4684DY	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 12V	Low Qgd ID=12A; rDS(on)=0.0135Ω Qgd = 2.8 nC;	SMD SO-8	
Si4686DY	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V Extremely Low Qgd WFET® Technology	Low Qgd ID=13.8A; rDS(on)=0.014Ω Qgd = 2.8 nC;	SMD SO-8	
Si4800BDY		N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 25V High-Efficient PWM Optimized	High VGS = ± 25V ID=9A; rDS(on)=0.030Ω Qgd= 3.5nC; VGSth= 0.8 V;	SMD SO-8	
Si4812BDY		N-Ch. 30-V (D-S) MOSFET w. SCHOTTKY With 1.4 A SCHOTTKY; VDS = 30V; VGS = ± 20V	VGS = ± 20V ID=9.5A; rDS(on)=0.021Ω Qgd= 2.6nC; VGSth= 1 V;	SMD SO-8	
Si4894BDY		N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V	Low Qgd ID=12A; rDS(on)=0.016Ω VGSth = 1 V	SMD SO-8	
Si7112DN	NEW	N-Ch. 30-V (D-S) Fast Switching MOSFET VDS = 30V; VGS = ± 12V Small package;	low Qgd, low rDS(on) ID=17.8A; rDS(on)=0.0082Ω Qgd= 3.1nC; VGSth= 0.6 V;	SMD PowerPAK 1212	
Si7230DN	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V PWM Optimized	Small package ID=14A; rDS(on)=0.016Ω Qgd= 4.3nC; VGSth= 1 V;	SMD PowerPAK 1212	
Si7326DN		N-Ch. 30-V (D-S) Fast Switching MOSFET VDS = 30V; VGS = ± 20V	Small package ID=10A; rDS(on)=0.030Ω Qgd= 3.5nC; VGSth= 0.8 V;	SMD PowerPAK 1212	
Si7386DP	NEW	N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 20V	Low Qgd, low rDS(on) ID=19A; rDS(on)=0.0095Ω Qgd = 3.0 nC	SMD PowerPAK SO-8	

Product Name	Status	Description	Features	Package	Q-Level
Si7392DP		N-Ch. Reduced Qg, Fast Switching WFET® VDS = 30V; VGS = ± 20V	Low Qgd ID=15A; rDS(on)=0.01375Ω Qgd = 2.6 nC	SMD PowerPAK SO-8	
Si7682DP	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V 100% Rg Tested	Low Qgd ID=17.5A; rDS(on)=0.013Ω Qgd = 3.1 nC;	SMD PowerPAK SO-8	
Si7686DP	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V Low Thermal Resistance PowerPAK®	Low Qgd ID=17.9A; rDS(on)= 0.014Ω Qgd = 2.8 nC;	SMD PowerPAK SO-8	

Inductors

Product Name	Status	Description	Features	Package	Q-Level
IHLP1616BZ-01	NEW	Inductor; High Current; Low Profile; Small Outline Package; Fully Shielded; Ultra Miniature Power	Profile height ≤ 2 mm; 0.47 μH to 4.7 μH; IDC up to 12.8 A;	SMD 1616 4.8x4.8x2.0mm	
IHLP2525CZ-01		Inductor; High Current; Low Profile; Small Outline Package; Fully Shielded; Miniature Power	Profile height ≤ 3 mm 0.1 μH to 10 μH IDC up to 60 A	SMD 2525 7.3x7.3x3.0mm	
IHLP4040DZ-01		Inductor; High Current; Low Profile; Small Outline Package; Fully Shielded;	Profile height ≤ 4mm 0.19 μH to 10 μH IDC up to 90 A	SMD 4040 11.5x11.5x4.0mm	
IHLP4040DZ-11		Inductor; High Current; Low Profile; Small Outline Package; Fully Shielded;	Profile height ≤ 4mm 0.19 μH to 100 μH IDC up to 46 A	SMD 4040 11.5x11.5x4.0mm	
IHLP5050CE-01		Inductor; High Current; Low Profile; Small Outline Package; Fully Shielded;	Profile height ≤ 3.5mm 0.1 μH to 10 μH IDC up to 84 A	SMD 5050 13.5x13.5x3.5mm	

Low-Side MOSFETs

Product Name	Status	Description	Features	Package	Q-Level
Si4336DY		N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V	Low rDS(on) ID=16.3A; rDS(on)=0.0067Ω VGStH = 1.0 V;	SMD SO-8	
Si4386DY		N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 20V	Low Qgd, low rDS(on) ID=16A; rDS(on)=0.0095Ω Qgd = 3.0 nC;	SMD SO-8	
Si4430BDY		N-Channel 30-V MOSFET VDS = 30V; VGS = ± 20V	Low rDS(on) ID=20A; rDS(on)=0.006Ω VGStH = 1.0 V;	SMD SO-8	
Si4634DY	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V	Low rDS(on), high Vast ID=16.3A; rDS(on)=0.0067Ω VGStH = 1.4 V;	SMD SO-8	
Si4682DY		N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V	VGS = ± 20V ID=12A; rDS(on)=0.0135Ω Qgd = 3.1 nC;	SMD SO-8	
Si4686DY		N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V Extremely Low Qgd WFET® Technology	VGS = ± 20V ID=13.8A; rDS(on)=0.014Ω Qgd = 2.8 nC;	SMD SO-8	
Si4800BDY		N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 25V High-Efficient PWM Optimized	High VGS = ± 25V ID=9A; rDS(on)=0.030Ω Qgd= 3.5nC; VGStH= 0.8 V;	SMD SO-8	
Si4812BDY		N-Ch. 30-V (D-S) MOSFET w. SCHOTTKY With 1.4 A SCHOTTKY; VDS = 30V; VGS = ± 20V	VGS = ± 20V ID=9.5A; rDS(on)=0.021Ω Qgd= 2.6nC; VGStH= 1 V;	SMD SO-8	
Si4874BDY	NEW	N-Channel 30-V MOSFET VDS = 30V; VGS = ± 20V	Low rDS(on) ID=16A; rDS(on)=0.0085Ω VGStH = 1 V	SMD SO-8	
Si7112DN	NEW	N-Ch. 30-V (D-S) Fast Switching MOSFET VDS = 30V; VGS = ± 12V Small package;	low Qgd, low rDS(on) ID=17.8A; rDS(on)=0.0082Ω Qgd= 3.1nC; VGStH= 0.6 V;	SMD PowerPAK 1212	

Product Name	Status	Description	Features	Package	Q-Level
Si7114DN	NEW	N-Ch. 30-V (D-S) Fast Switching MOSFET VDS = 30V; VGS = ± 20V TrenchFET® Gen II Power MOSFET	Small package ID=18.3A; rDS(on)=0.010Ω Qgd= 3.6nC; VGSth= 1 V;	SMD PowerPAK 1212	
Si7230DN	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V PWM Optimized	Small package ID=14A; rDS(on)=0.016Ω Qgd= 4.3nC; VGSth= 1 V;	SMD PowerPAK 1212	
Si7326DN	NEW	N-Ch. 30-V (D-S) Fast Switching MOSFET VDS = 30V; VGS = ± 20V	Small package ID=10A; rDS(on)=0.030Ω Qgd= 3.5nC; VGSth= 0.8 V;	SMD PowerPAK 1212	
Si7336 ADP	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V Ultra Low (ON) Resistance;	Low rDS(on) ID=30A; rDS(on)=0.0040Ω VGSth = 1 V	SMD PowerPAK SO-8	
Si7634BDP	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V	Low rDS(on), high Vast ID=23A; rDS(on)=0.0076Ω VGSth = 1.5 V	SMD PowerPAK SO-8	
Si7636DP	NEW	N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V Ultra Low (ON) Resistance	Low rDS(on) ID=28A; rDS(on)=0.0048Ω VGSth = 1 V	SMD PowerPAK SO-8	

Resistors

Product Name	Status	Description	Features	Package	Q-Level
WSL2010-18		1 Watt Current sensing Resistor Power Metal Strip® Resistors; Low Resistance Value;	High power & reliability R=0.001Ω to 0.2Ω TCR ≤ 20ppm	SMD 2010 5.08x2.54x0.635	
WSL2512-18		2 Watt Current sensing Resistor Power Metal Strip® Resistors; Low Resistance Value;	High power & reliability R=0.001Ω to 0.2Ω TCR ≤ 20ppm	SMD 2512 6.36x3.18x0.635	
WSLP1206	NEW	1 Watt Power Metal Strip® Resistors; Very High Power- Small Size; Current Sensing;	High power & reliability R=0.001Ω to 0.2Ω	SMD 1206 3.2x1.6x0.635mm	

Schottky Diodes

Product Name	Status	Description	Features	Package	Q-Level
B140		Schottky Barrier Rectifier; Low Profile; Guardring for overload protection; High Surge Capabilities;	VRRM = 40 V; IF = 1 A, VF = 0.52 V,	SMD DO-214AC (SMA) 5.28x2.8x2.3mm	
B240 A		High-Current Density Schottky Rectifier High Efficiency; Low Power Loss; Low Profile	VRRM = 40 V; IF = 2 A, VF = 0.5 V,	SMD DO-214AC (SMA) 5.28x2.8x2.3mm	
B340 A		High-Current Density Schottky Rectifier High Efficiency; Low Power Loss; RoHS-Compliant	VRRM = 40 V; IF = 3A, VF = 0.5 V,	SMD DO-214AC (SMA) 5.28x2.8x2.3mm	
MSS1P4		Schottky Barrier Rectifiers SMD; #SMP# Series;	VRRM = 40 V; IF = 1 A; VF = 0.41 V;	SMD MicroSMP 2.7x1.4x0.75mm	
SS1P4	NEW	Schottky Barrier Rectifiers; SMD; High Current Density; #SMP# Series;	Small package VRRM = 40 V; IF = 2 A, VF = 0.4 V,	SMD DO-220AA (SMP) 4x2.18x1.15mm	
SS2P4	NEW	Schottky Barrier Rectifiers; SMD; High Current Density; #SMP# Series;	Small package VRRM = 40 V; IF = 2 A, VF = 0.43 V,	SMD DO-220AA (SMP) 4x2.18x1.15mm	
SS3P4	NEW	Schottky Barrier Rectifiers; SMD; High Current Density;#SMP# Series;	Small package VRRM = 40 V; IF = 3A, VF = 0.5 V,	SMD DO-220AA (SMP) 4x2.18x1.15mm	

Small-Signal MOSFET

Product Name	Status	Description	Features	Package	Q-Level
2N7002K		N-Ch 60-V (D-S)MOSFET; 2KV ESD protected Low On-Resistance; Low Threshold;	VDS = 60 V; VGS = 20 V; rDS(on) = 4 Ohms, ID = 0.3A, VGSth = 1 V	SMD TO-236 (SOT-23)	

Product Name	Status	Description	Features	Package	Q-Level
		Low Input Capacitance; Fast Switch			

Switch Diodes

Product Name	Status	Description	Features	Package	Q-Level
1N4148WS-V		Small Signal Fast Switching Diode; Silicon epitaxial planar diode; RoHS-Compliant;	VRRM = 75 V; IF = 0.15A; VF = 1.2 V;	SMD SOD323 2.85x1.5x1.15mm	
BAT54 A		Schottky Barrier Diode; DUAL; Miniature; for high speed switching; clamping; and circuit protection.	Dual, VRRM = 30 V; IF = 0.2 A, VF = 0.5 V,	SMD TO-236 (SOT-23) 3.1x2.6x1.15mm	Std.
BAT54 A-V		Small Signal Schottky Diodes; Single & Dual Schematics; Very Low Turn-On and Fast Switching	Dual, VRRM = 30 V; IF = 0.2 A, VF = 0.8 V,	SMD TO-236 (SOT-23) 3.0x2.5x1.1mm	Thin Pack
BAT54 AW		Schottky Barrier Diode; DUAL; Miniature;	DUAL;VRRM = 30 V, IF = 0.2 A, VF = 0.5 V,	SMD SOT-323 2.2x2.2x1.0mm	
MBR0530		Schottky Diodes; Fast Switching; Ultra Low Forward Voltage drop;	VRRM = 30 V; IF = 0.5 A, VF = 0.35 V;	SMD SOD123 3.85x1.7x1.35mm	

Notebook : SYSTEM HARDWARE, IrDA Transceiver

FIR

Product Name	Status	Description	Features	Package	Q-Level
TFDU6103		Infrared Transceiver FIR 4M bit/S, SMD BabyFace type	FIR 4M bit/S,	SMD Baby Face	
TFDU6300	NEW	Infrared Transceiver FIR 4M bit/S, SMD type, Low Profile ≤ 2.7 mm	FIR 4M bit/S,	SMD	

SIR

Product Name	Status	Description	Features	Package	Q-Level
TFBS4101	NEW	Infrared Transceiver , SIR 115 kbit/s; SMD type, Low Profile ≤ 2.6 mm	SIR 115 kbit/s;	SMD	
TFBS4711		Infrared Transceiver , SIR 115 kbit/s; SMD type, Low Profile ≤ 1.9 mm	SIR 115 kbit/s;	SMD	
TFDU4300		Infrared Transceiver , SIR 115 kbit/s; SMD type, Low Profile ≤ 2.5 mm	SIR 115 kbit/s;	SMD	

Notebook : SYSTEM HARDWARE, Load Switch

Level Shift

Product Name	Status	Description	Features	Package	Q-Level
Si1865DL	NEW	Load Switch with Level-Shift; With 2-kV ESD Protection Low Profile; Small Footprint	VDS = 8 V; ID=1.2A; rDS(on)=0.215Ω; Von/off = 8 V;	SMD SC-70	
Si3865BDV		Load Switch with Level-Shift; With 3-kV ESD Protection;1.8 Volt Rated; VDS = 8V	Lower turn-on at 1.8 V ID=2.9A; rDS(on)=0.060Ω; Von/off = 8 V,	SMD TSOP-6	

MOSFETs

Product Name	Status	Description	Features	Package	Q-Level
2N7002K		N-Ch 60-V (D-S)MOSFET; 2KV ESD protected Low On-Resistance; Low Threshold; Low Input Capacitance; Fast Switch	VDS = 60 V; VGS = 20 V; rDS(on) = 4 Ohms, ID = 0.3A, VGStH = 1 V	SMD TO-236 (SOT-23)	
Si3424DV		N-Channel 30-V (D-S) MOSFET TrenchFET® Power MOSFETS	VGS = ± 20V ID=6.7A; rDS(on)=0.038Ω; Qgd= 11.5nC; VGStH= 0.8V;	SMD TSOP-6	
Si3433BDC		P-Channel 1.8-V (G-S) MOSFET TrenchFET® Power MOSFETS	VGS = ± 8V ID=5.6A; rDS(on)=0.042Ω; Qgd= 12nC; VGStH= 0.45 V;	SMD TSOP-6	
Si3442BDV		N-Channel 2.5-V (G-S) MOSFET VDS = 20V; VGS = ± 12V	VGS = ± 12V ID=4.2A; rDS(on)=0.090Ω; Qgd= 3.0nC; VGStH= 0.6 V;	SMD TSOP-6	
Si3456BDV		N-Channel 30-V (D-S) MOSFET VDS = 30V; VGS = ± 20V	VGS = ± 20V ID=6A; rDS(on)=0.052Ω; Qgd= 8.6nC; VGStH= 1 V;	SMD TSOP-6	
Si4800BDY		N-Ch. Reduced Qg, Fast Switching MOSFET VDS = 30V; VGS = ± 25V High-Efficient PWM Optimized	High VGS = ± 25V ID=9A; rDS(on)=0.030Ω Qgd= 3.5nC; VGStH= 0.8 V;	SMD SO-8	
Si7326DN	NEW	N-Ch. 30-V (D-S) Fast Switching MOSFET VDS = 30V; VGS = ± 20V	VGS = ± 20V ID=10A; rDS(on)=0.030Ω Qgd= 3.5nC; VGStH= 0.8 V;	SMD PowerPAK 1212	
TP0610K		P-Channel 60-V (D-S) MOSFET With 2-kV ESD Protection; VDS = 60 V, VGS = 20 V,	ID=0.185A; rDS(on)=10Ω VGStH = 1 V	SMD SOT-23	

Slew Rate control

Product Name	Status	Description	Features	Package	Q-Level
SiP4282 A-1/3	NEW	1.2 A Slew Rate Controlled Load Switch	1.2A Switch Current rDS(on)= 0.230 Ω 1: 1mS / 3: 100uS	SMD SC-75 PowerPAK	

With Current Limit

Product Name	Status	Description	Features	Package	Q-Level
SiP4612 A/B	NEW	Protected 1-A High-Side Load Switch A: active low / B: active high	1-A current limit rDS(on)= 0.225 Ω	SMD TSC-75 PowerPAK	

Notebook : SYSTEM HARDWARE, Opto Sensor

Ambient Light Sensor

Product Name	Status	Description	Features	Package	Q-Level
TEMT6000X01	NEW	NPN Phototransistor; Ambient Light Sensor;		SMD 4.0x2.0x1.05mm	
TEMT6200FX01	NEW	NPN Phototransistor; Ambient Light Sensor;		SMD 0805 EIA-Sizes	

IR Receiver Module

Product Name	Status	Description	Features	Package	Q-Level
TSOP-62XX		Infrared remote control receiver module; SMD type, 5 V		SMD	
TSOP348XX		Infrared remote control receiver module, DIP molded type, 3 V		TH / DIP	
TSOP362XX	NEW	Infrared remote control receiver module, SMD type, 3 V		SMD	
TSOP382XX	NEW	Infrared remote control receiver module, DIP Minicast type, 3 V		TH / DIP	
TSOP48XX		Infrared remote control receiver module, DIP molded type, 5 V		TH / DIP	

Notebook : SYSTEM HARDWARE, Protection

Diodes

Product Name	Status	Description	Features	Package	Q-Level
1N4148WS-V		Small Signal Fast Switching Diode; Silicon epitaxial planar diode; RoHS-Compliant;	VRRM = 75 V; IF = 0.15A; VF = 1.2 V;	SMD SOD323 2.85x1.5x1.15mm	
BAT54 A		Schottky Barrier Diode; DUAL; Miniature; for high speed switching; clamping; and circuit protection.	Dual, VRRM = 30 V; IF = 0.2 A, VF = 0.5 V,	SMD TO-236 (SOT-23) 3.1x2.6x1.15mm	Std.
BAT54 A-V		Small Signal Schottky Diodes; Single & Dual Schematics; Very Low Turn-On and Fast Switching	Dual, VRRM = 30 V; IF = 0.2 A, VF = 0.8 V,	SMD TO-236 (SOT-23) 3.0x2.5x1.1mm	Thin Pack
BAT54 AW		Schottky Barrier Diode; DUAL; Miniature;	DUAL;VRRM = 30 V, IF = 0.2 A, VF = 0.5 V,	SMD SOT-323 2.2x2.2x1.0mm	
BAV99-V		Small Signal Switching Diode, Dual	Dual; VRRM = 70 V, IF = 0.2A; VF = 0.715 V	SMD SOT-23	
MBR0530		Schottky Diodes; Fast Switching; Ultra Low Forward Voltage drop;	VRRM = 30 V; IF = 0.5 A, VF = 0.35 V;	SMD SOD123 3.85x1.7x1.35mm	

EMI

Product Name	Status	Description	Features	Package	Q-Level
ILHB series		Ferrite beads@100MHz; High Current; EIA-Size = 0603/0805/1206/1812	High current current 2 A to 3 A DCR = 0.1~0.05 ohms,	SMD 0402 to 1206 EIA-Sizes	

ESD

Product Name	Status	Description	Features	Package	Q-Level
GMF05 series	NEW	ESD Protection Diode Array; Small Size; Five Channels Array	Cj = 150 pF; Ipp = 12 A; 200W; Vclamping = 12.5 V;	SMD	
VESD05 series	NEW	ESD Protection Diode Array; Compact; Depends on ESD test condition		SMD	

ESD for Bus

Product Name	Status	Description	Features	Package	Q-Level
VBUS05 series	NEW	BUS-port ESD-protection Array; Ultra Compact;Multi-Channel	Low capacitance Cd <1 pF	SMD	

ESD+EMI

Product Name	Status	Description	Features	Package	Q-Level
VEMI Series	NEW	EMI-Filter with ESD-Protection; Multi-Channel Depends on 3 factors: Rs / BW / Cap.		SMD	

Fuse

Product Name	Status	Description	Features	Package	Q-Level
MFU0603	NEW	Fuses, Thin Film; Fast Acting; 0603; Stable Fusing Characteristics;	IR = 0.5 A to 5.0 A; UDCmax = 32 V	SMD 0603 EIA-Sizes	
MFU0805	NEW	Fuses, Thin Film; Fast Acting; 0805; Stable Fusing Characteristics;	IR = 0.5 A to 5.0 A; UDCmax = 32 V	SMD 0805 EIA-Sizes	

Thermister NTC

Product Name	Status	Description	Features	Package	Q-Level
2381 615 1xxx		NTC Thermistors; Surface Mount;	2 k Ω -470	SMD	

Product Name	Status	Description	Features	Package	Q-Level
		TCR from 6 to 2% even at higher temp. RoHS-Compliant;	% Rtol.@25°C ≤ 5 %; Ptot = 0.21 W	0805 EIA-Sizes	
2381 615 2xxx		NTC Thermistors; Surface Mount; Temperature Compensation	4.7 kΩ-100 kΩ; RTol.@25°C ≤ 5 %; P=0.125 W; B25/85Tol.=1%	SMD 0603 EIA-Sizes	
2381 615 3xxx		NTC Thermistors; Surface Mount; Tolerance on B25/85 down to 1 %	2.2 kΩ to 100 kΩ; 0.125 W RTol.@25°C = 5% to 1 %;	SMD 0603 EIA-Sizes	
2381 615 4xxx		NTC Thermistors; Surface Mount; Tolerance on B25/85 down to 1 %	4.7 kΩ to 100 kΩ; 0.125 W RTol.@25°C = 5% to 1 %;	SMD 0402 EIA-Sizes	
2381 615 5xxx		NTC Thermistors; Surface Mount; Tolerance on B25/85 down to 1 %	2.2 kΩ to 680 kΩ, 0.21 W RTol.@25°C = 10% to 2 %;	SMD 0805 EIA-Sizes	
NTHS		NTC Thermistors; Monolithic Construction	R25 = 1 kΩ to 330 kΩ Tol.@25°C = 10 % to 1% B(25/75) = 3181 to 4247	SMD 0402 to 1206 EIA-Sizes	

Thermister PTC

Product Name	Status	Description	Features	Package	Q-Level
PTFT		PTC Thermistors; Linear; Thick Film; Linear from -55°C to +125°C;	TCR = 2300 to 3500 ppm R25 = 10R to 10 kΩ TCR Tol. = ±400 ppm	SMD 0603 to 1206 EIA-Sizes	
TFPT		PTC Thermistors; Linear; Thin Film; SMD; EIA 0603/0805/1206;	TCR@25°C= 4110ppm TCR Tol.=±400ppm	SMD 0603 to 1206 EIA-Size	

TVS

Product Name	Status	Description	Features	Package	Q-Level
MSP5.0	NEW	TRANSZORB® Transient Voltage Suppressors SMD; #SMP# Series;	Ultra small-package 100W; 10.9 A; Vclamping = 5 V	SMD MicroSMP 2.7x1.4x0.75mm	
TPSMP series		Transient Voltage Suppressor High Power Density; SMD; Automotive Qualified	Small package 400 W, up to 30 A, VF = 2.5 V,	SMD SMP 4x2.18x1.15mm	AEC Q-101

Zener

Product Name	Status	Description	Features	Package	Q-Level
BZX384 series		Silicon Planar Power Zener Diodes; Miniature;	0.2 Watt Zvoltage Tol. ≤ 5%	SMD SOD323 2.85x1.5x1.15mm	
BZX584 series		Silicon Planar Power Zener Diodes; Ultra Miniature	0.2 Watt Zvoltage Tol. ≤ 5%	SMD SOD523 1.6x0.8x0.6mm	

